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DISCRETE SEMICONDUCTORS

DATA SHEET

BFG10W/XUHF power transistor

Product specification

1995 Sep 22



UHF power transistor

BFG10W/X

FEATURES

- High efficiency
- Small size discrete power amplifier
- 900 MHz and 1.9 GHz operating areas
- Gold metallization ensures excellent reliability.

APPLICATIONS

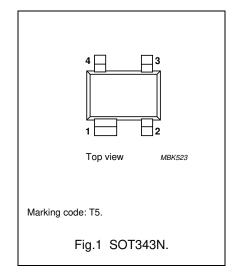
 Common emitter class-AB operation in hand-held radio equipment up to 1.9 GHz.

DESCRIPTION

NPN silicon planar epitaxial transistor encapsulated in a plastic, 4-pin dual-emitter SOT343N package.

PINNING

PIN	DESCRIPTION			
1	collector			
2	emitter			
3	base			
4	emitter			



QUICK REFERENCE DATA

RF performance at T_{amb} = 25 °C in a common-emitter test circuit.

MODE OF OPERATION	f (GHz)	V _{CE} (V)	P _L (mW)	G _p (dB)	η _c (%)
Pulsed, class-AB, duty cycle: $< 1 : 2; t_p = 10 \text{ ms}$	1.9	3.6	200	≥5	≥50
Pulsed, class-AB, duty cycle: $< 1 : 8; t_p = 4.6 \text{ ms}$	0.9	6	650	≥10	≥50
	0.9	6	360	≥12.5	≥50

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	20	V
V_{CEO}	collector-emitter voltage	open base	_	10	V
V_{EBO}	emitter-base voltage	open collector	_	2.5	V
Ic	collector current (DC)		_	250	mA
I _{C(AV)}	average collector current		_	250	mA
P _{tot}	total power dissipation	up to T _s = 102 °C; note 1	_	400	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	175	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	up to $T_s = 102$ °C; note 1; $P_{tot} = 400$ mW	180	K/W

Note to the Limiting values and Thermal characteristics

1. T_s is the temperature at the soldering point of the collector pin.

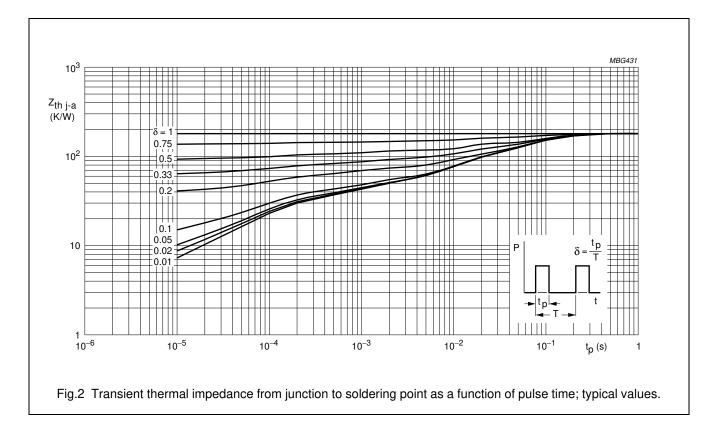
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CHARACTERISTICS

 T_j = 25 °C (unless otherwise specified).

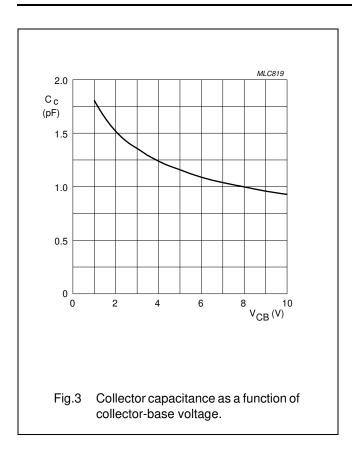
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; I _C = 0.1 mA	20	_	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; I _C = 5 mA	10	_	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; I _E = 0.1 mA	2.5	_	V
I _{CES}	collector cut-off current	$V_{CE} = 6 \text{ V}; V_{BE} = 0$	_	100	μΑ
h _{FE}	DC current gain	$I_C = 50 \text{ mA}; V_{CE} = 5 \text{ V}$	25	_	
C _c	collector capacitance	$I_E = i_e = 0; V_{CB} = 6 V; f = 1 MHz$	_	3	pF
C _{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 6 \text{ V}$; $f = 1 \text{ MHz}$	_	2	pF



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APPLICATION INFORMATION

RF performance at T_{amb} = 25 °C in a common-emitter test circuit.

MODE OF OPERATION	f (GHz)	V _{CE} (V)	P _L (mW)	G _p (dB)	η _c (%)
Pulsed, class-AB, duty cycle: $< 1 : 2; t_p = 10 \text{ ms}$	1.9	3.6	200	≥5; typ. 7	≥50; typ. 60
Pulsed, class-AB, duty cycle: < 1 : 8; t _p = 5 ms	0.9	6	650	≥10	≥50
	0.9	6	360	≥12.5	≥50

Ruggedness in class-AB operation

The BFG10W/X is capable of withstanding a load mismatch corresponding to VSWR = 6:1 through all phases under pulsed conditions up to a supply voltage of 8.6 V under the conditions: 900 MHz; 650 mW; $t_p = 4.6$ ms; duty cycle of 1:8 and up to a supply voltage of 5.5 V under the conditions: 1.9 GHz; 200 mW; $t_p = 10$ ms; duty cycle of 1:2.

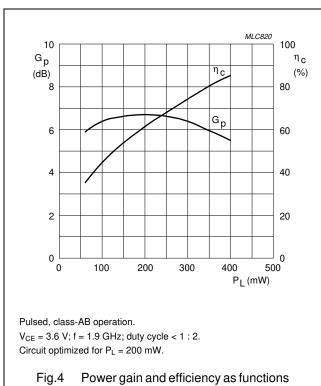


Fig.4 Power gain and efficiency as functions of load power; typical values.

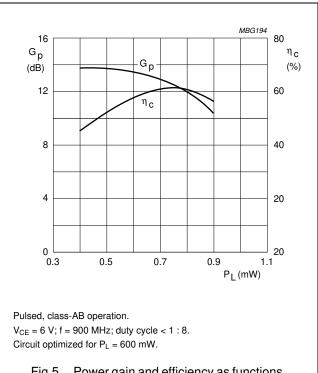


Fig.5 Power gain and efficiency as functions of load power; typical values.

UHF power transistor

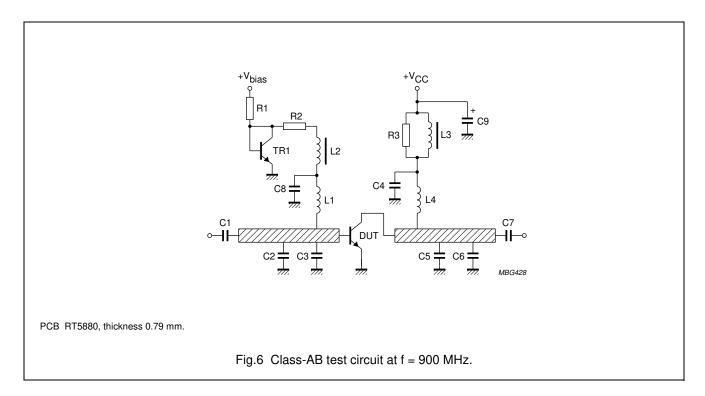
BFG10W/X

List of components (see Fig.6)

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
TR1	bias transistor, BC548 or equivalent	note 1		
C1, C4, C7	capacitor; notes 2 and 3	120 pF		
C2	capacitor; note 2	6.8 pF		
C3	capacitor; note 2	0.5 pF		
C5	capacitor; note 2	1.2 pF		
C6	capacitor; note 2	1.9 pF		
C8	Philips multilayer capacitor	1 nF, 10 V		
C9	Philips capacitor	1500 μF, 10 V		2222 032 14152
L1	6 turns enamelled 0.7 mm copper wire		length 3.5 mm	
L4	2 turns enamelled 0.7 mm copper wire		length 3 mm	
L2, L3	RF choke, Philips			4312 020 36690
R1	metal film resistor	275 Ω		
R2	metal film resistor	100 Ω		
R3	metal film resistor	10 Ω		

Notes

- 1. V_{BE} at 1 mA must be 0.65 V.
- 2. American Technical Ceramics type 100A or capacitor of same quality.
- 3. Resonant at 1900 MHz.



UHF power transistor

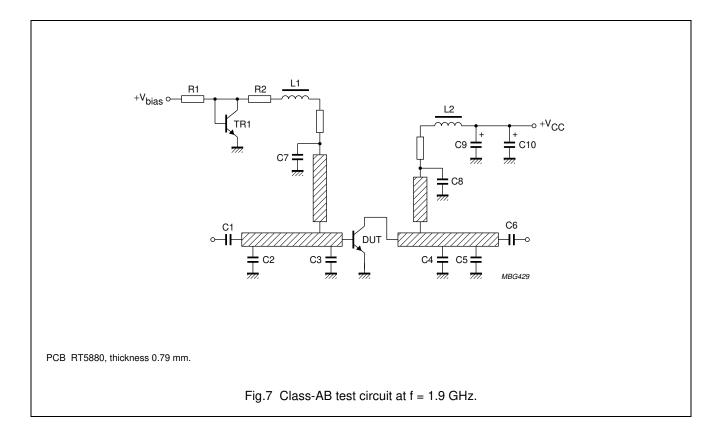
BFG10W/X

List of components (see Fig.6)

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
TR1	bias transistor, BC548 or equivalent	note 1		
C1, C6, C7, C8	capacitor; notes 2 and 3	24 pF		
C2	capacitor; note 2	0.4 pF		
C3	capacitor; note 2	2.4 pF		
C4	capacitor; note 2	0.5 pF		
C5	capacitor; note 2	1.2 pF		
C9, C10	Philips capacitor	1500 μF, 10 V		2222 032 14152
L1, L2	RF choke, Philips			4330 030 36301
R1, R2	metal film resistor	75 Ω		
R3, R4	metal film resistor	10 Ω		

Notes

- 1. V_{BE} at 1 mA must be 0.65 V.
- 2. American Technical Ceramics type 100A or capacitor of same quality.
- 3. Resonant at 1900 MHz.



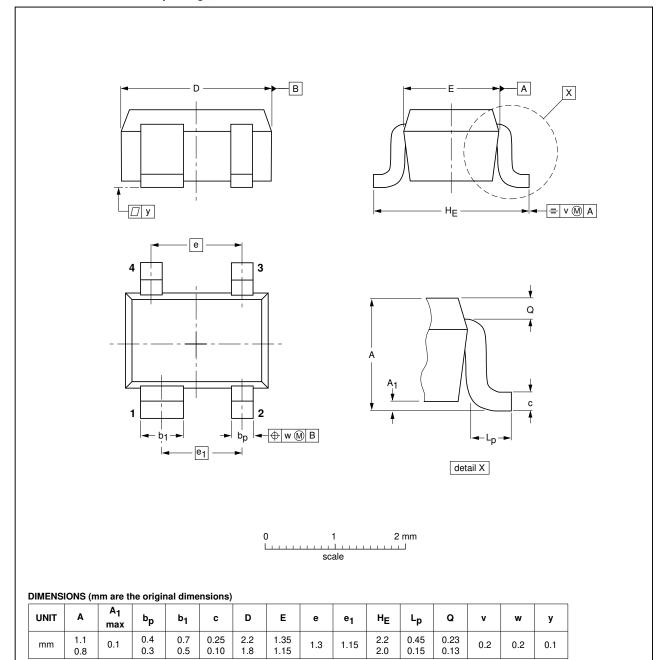
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PACKAGE OUTLINE

Plastic surface-mounted package; 4 leads

SOT343N



OUTLINE		REFERENCES			EUROPEAN ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT343N						97-05-21 06-03-16

UHF power transistor

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DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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